a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region;

a second conductive layer formed on said first conductive layer; and

C1

an insulating film comprising anodization oxide of said first and second conductive layers,

Concl'd

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein an anodization rate of said first conductive layer is greater than that of said second layer so that a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

SUB F2

6. (Amended) A semiconductor device comprising:

C2

a semiconductor layer comprising a source region, a drain region, and a channel region formed on an insulating surface;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region;

a second conductive layer formed on said first conductive layer; and

an insulating film comprising anodization oxide of said first and second conductive layers,

C2 Concl'd

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein an anodization rate of said first conductive layer is greater than that of said second layer so that a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on side surfaces of said first and second conductive layers and a top surface of said second conductive layer.

Sub D1 C3

11. (Amended) A semiconductor device comprising:

a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region;

a second conductive layer electrically connected to said first conductive layer; and

C3

an insulating film comprising oxide of said first and second conductive layers,

Concl'd

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

Sub D3

16. (Amended) A semiconductor device comprising:

a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

C4

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region;

a second conductive layer electrically connected to said first conductive layer wherein said first conductive layer

comprises a different material from said first conductive layer; and

an insulating film comprising oxide of said first and second conductive layers,

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on side surfaces of said first and second conductive layers and a top surface of said second conductive layer.

21. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

an insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film,

wherein said first layer and said second layer comprises a material selected from the group consisting of molybdenum,

tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer.

25. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

a gate insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film, and

an insulating film comprising oxide of said first and second conductive layers;

wherein said first layer and said second layer comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

Please add the following new claims 29-38.

--29. (New) A semiconductor device according to claim 11, wherein said insulating film comprises anodization oxide of said first and second conductive layers.

30. (New) A semiconductor device according to claim 16, wherein said insulating film comprises anodization oxide of said first and second conductive layers.

31. (New) A semiconductor device according to claim 25, wherein said insulating film comprises anodization oxide of said first and second conductive layers.

32. (New) A semiconductor device according to claim 25, wherein said insulating film is further formed on a top surface of said second conductive layer.

33. (New) A semiconductor device according to claim 1, wherein said first conductive layer comprises tantalum and said second layer comprises aluminum.

34. (New) A semiconductor device according to claim 6, wherein said first conductive layer comprises tantalum and said second layer comprises aluminum.

35. (New) A semiconductor device according to claim 11, wherein said first conductive layer comprises tantalum and said second layer comprises aluminum.

36. (New) A semiconductor device according to claim 16, wherein said first conductive layer comprises tantalum and said second layer comprises aluminum.

37. (New) A semiconductor device according to claim 21, wherein said first conductive layer comprises aluminum and said second layer comprises tantalum.

38. (New) A semiconductor device according to claim 25, wherein said first conductive layer comprises aluminum and said second layer comprises tantalum.--

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REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested. The foregoing amendments are responsive to the December 21, 2000 Office Action. Applicants respectfully request entry of the requested amendments and reconsideration of the application in view of the following comments.